

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) YO999-408 CIP		Application Number Not Yet Assigned	
				Applicant(s) Cohen et al.			
				Filing Date Concurrently Herewith		Group Art Unit Not Yet Assigned	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EK	6,054,386	04/2000	Prabhakar	—	—	—	PRO
EK	6,169,005	01/2001	Kepler	—	—	—	U.S. 09/902483 07/11/01
EK	5,994,191	11/1999	Xiang	—	—	—	09/902483 07/11/01
FOREIGN PATENT DOCUMENTS							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
—	—	—	—	—	—	YES	NO
—	—	—	—	—	—	—	—
—	—	—	—	—	—	—	—
—	—	—	—	—	—	—	—
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
EXAMINER	<i>Erik Kiehr</i>			DATE CONSIDERED		2/1/02	

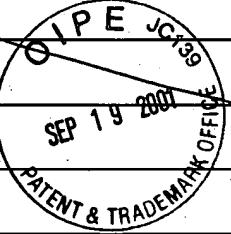
EXAMINER

Erik Riehl

DATE CONSIDERED

2/1/02

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and consider. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION <small>(Use several sheets if necessary)</small>				Docket Number (Optional) YO999-4444-1111		Application Number 09/902,483	
				Applicant(s) Cabral, Jr., et al.			
				Filing Date July 11, 2001		Group Art Unit 2813	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>EL</i>		5,773,331	6/30/98	Solomon et al.	—	—	
<i>EL</i>		4,912,542	3/27/90	Suguro	—	—	
<i>EL</i>		4,443,930	4/24/84	Hwang et al.	—	—	
<i>EL</i>		5,962,893	10/5/99	Omura et.al.	—	—	
							
FOREIGN PATENT DOCUMENTS							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
						YES	NO
						YES	NO
						YES	NO
						YES	NO
						YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
<i>EL</i>		U.S. Patent Application No. 09/515,033, Y0R900-0044US1, "Method For Self-Aligned Formation Of Silicide Contacts Using Metal Silicon Alloys For Limited Silicon Consumption And For Reduction Of Bridging", pp. 1-21, and Figs. 1A-3B. now U.S. Patent 6,323,130					
<i>EL</i>		Lisa T. Su, Melanie J. Sherony, Hang Hu, James E. Chung, and Dimitri A. Antoniadis; "Optimization of Series Resistance in Sub-0.2, um SOI MOSFET's; IEEE Electron Device Letters, Vol. 15, No. 9, September 1994; pages 363-365.					
EXAMINER <i>Eric Kuhn</i>				DATE CONSIDERED 2/1/02			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

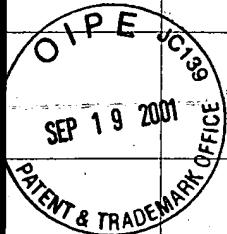
Docket Number (Optional)	YO999-4 TIP	Application Number 09/902,483
Applicant(s) Cabral, Jr. et al.		
Filing Date July 11, 2001	Group Art Unit 2813	

*EXAMINER
INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EK T. Yoshitomi, M. Saito, T. Ohguro, M. Ono, H.S. Momose, and H. Iwai; "Silicided Silicon-Sidewall Source and Drain (S4D) structure for high-performance 75-nm gate length pMOSFETs; 1995 Symposium on VLSI Technology Digest of Technical Papers; 0-7803-2602-4/95; pages 11 and 12.

EK T. Yachi and S. Suyama; "A New Method Utilizing Ti-Silicide Oxidation for the Fabrication of a MOSFET with a Self-Aligned Schottky Source/Drain"; IEEE Electron Device Letters, Vol EDL-4, No. 8, August 1983; pages 277-279; and "Silicides for VLSI Applications"; S.P. Murarka; pages 138-141.



EXAMINER

Erik Kuhn

DATE CONSIDERED

2/1/02

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.